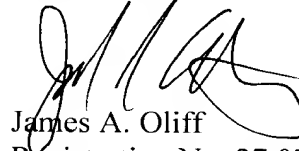


REMARKS

The attached Appendix includes marked-up copies of each rewritten paragraph (37 C.F.R. §1.121(b)(1)(iii)).

Respectfully submitted,

  
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## APPENDIX

## Changes to Specification:

Page 23, lines 6-17:

Next, when the working reticle WR is illuminated by the illumination optical system 31 and the reduced image of this pattern is transferred onto the wafer W through the projection optical system 33 as shown in Fig. 4, deformation of some extent of the projected image by the optical proximity effect, and by extension deformation of a pattern to be formed are generated. Especially when a pattern to be transferred is a fine dense pattern, there is an adverse possibility that the deformation amount exceeds a predetermined tolerance. Thereupon, in this example, the influence of the optical proximity effect is corrected as will be explained with reference to ~~Fig. 2~~ Figs. 2A, 2B1, 2B2, 2C1 and 2C2.